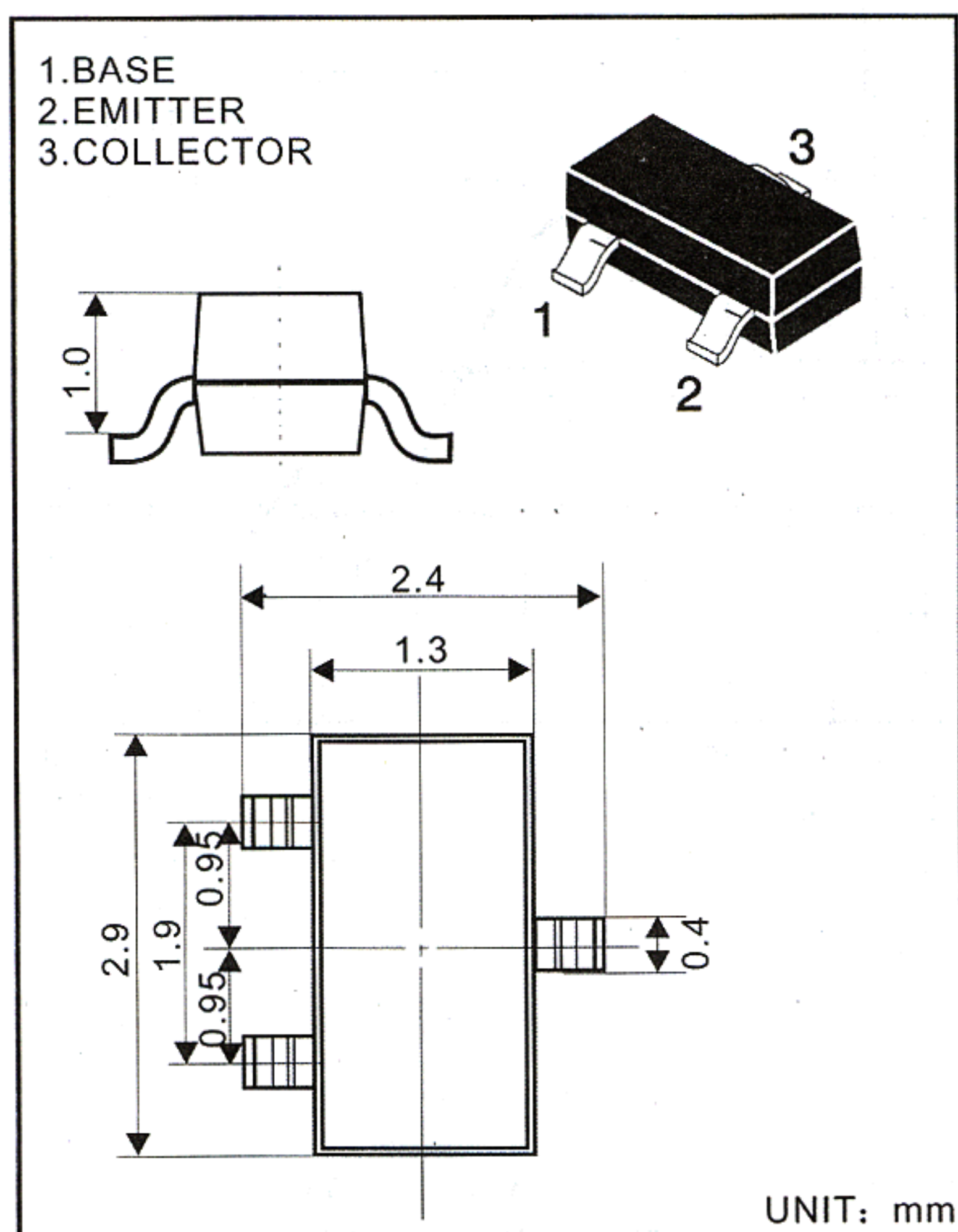


MMBTA92LT1 TRANSISTOR (PNP)



FEATURES

Power dissipation

P_{CM} : 0.3 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.3 A

Collector-base voltage

$V_{(BR)CBO}$: -300V

Operating and storage junction temperature range

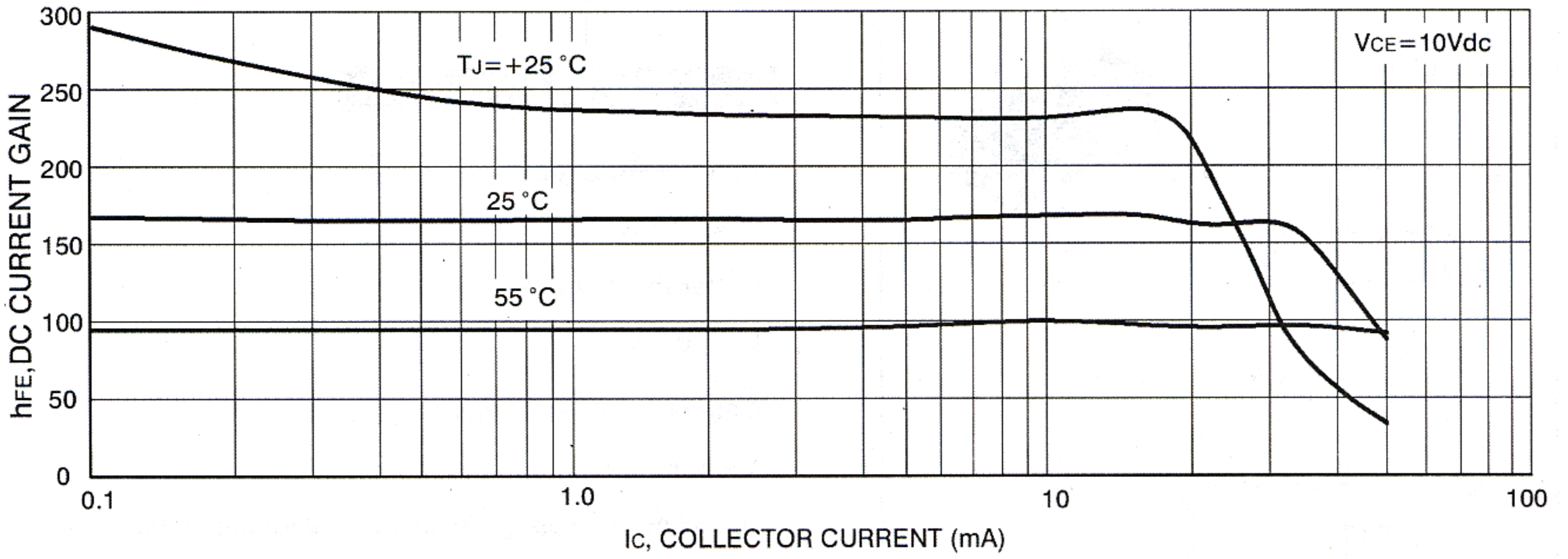
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

ELECTRICAL CHARACTERISTICS

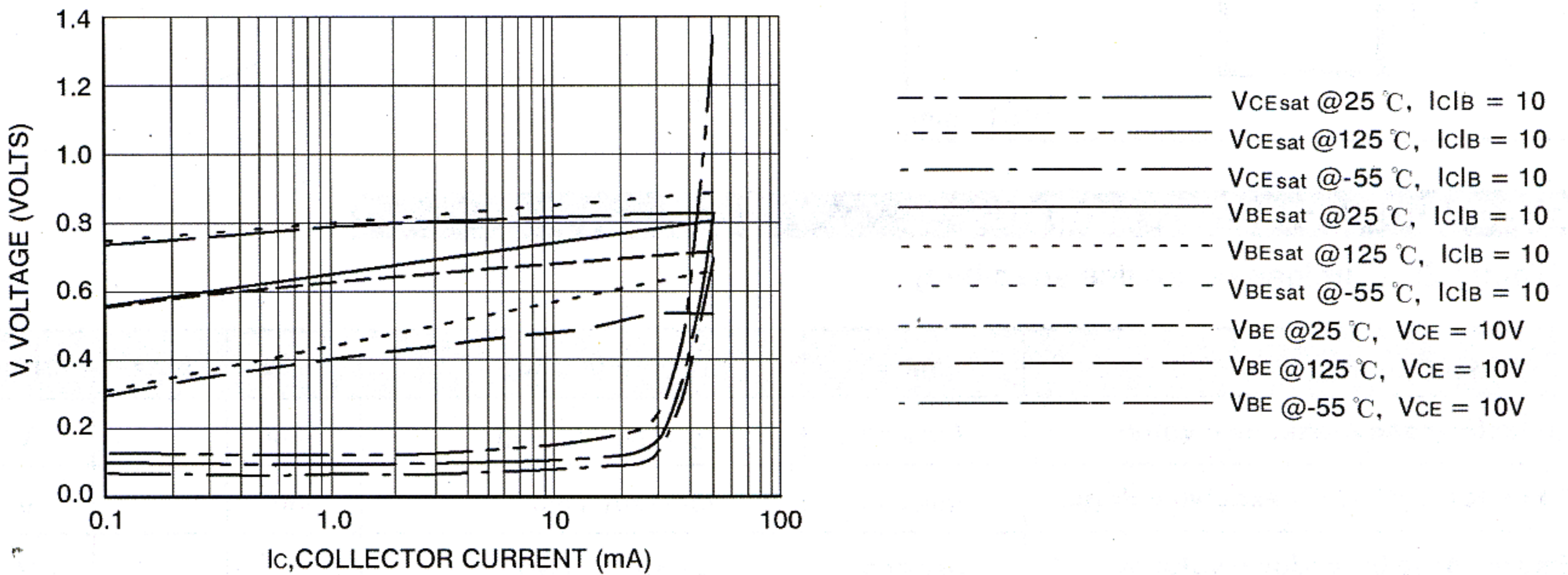
($T_{amp}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-300		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-300		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-10\mu A, I_B=0$	-5		V
Collector cut-off current	I_{CBO}	$V_{CB}=-200V, I_E=0$		-0.25	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-3V, I_C=0mA$		-0.25	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-10V, I_C=-1mA$	25		
	$h_{FE(2)}$	$V_{CE}=-10V, I_C=-10mA$	100	200	
	$h_{FE(3)}$	$V_{CE}=-10V, I_C=-50mA$	25		
Collector-emitter saturation voltage	V_{CEsat}	$I_C=-20mA, I_B=-2mA$		-0.5	V
Base-emitter saturation voltage	V_{BEsat}	$I_C=-20mA, I_B=-2mA$		-0.9	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-10mA, f=30MHz$	50		MHz

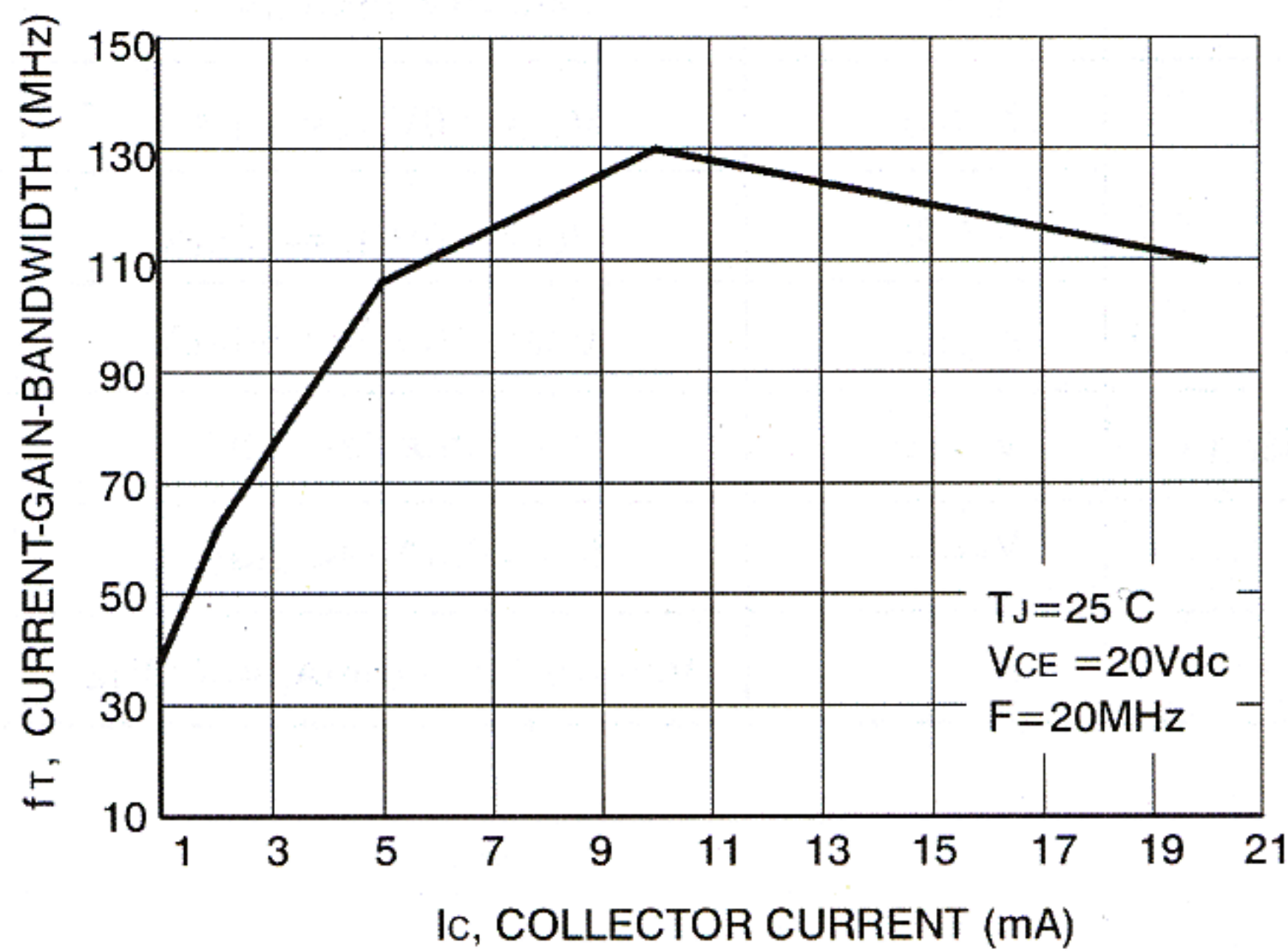
DEVICE MARKING : MMBTA42LT1=2D



DC Current Gain



"ON" Voltages



Current-Gain — Bandwidth